

Supplementary Information:

Colloidal Synthesized MoSe₂/Graphene Hybrid Nanostructures as Efficient Electrocatalysts for Hydrogen Evolution

Zhengqing Liu, Na Li, Hongyang Zhao, Yaping Du*

Experimental Section

Materials Synthesis

Synthesis of 3D structures assembled from layered MoSe₂: A typical procedure is described as follows: a given amount of (NH₄)₂MoO₄ (0.5 mmol) and selenium powder (1.0 mmol) was added in 18 mL mixture of oleic acid and ethanol (volume ratio=1:1) in a 20 mL Teflon-lined autoclave. The autoclave was sealed and heated at 160-200 °C for 72 h in an oven, and then cooled down to room temperature. The products were collected by centrifugation and washed several times with ethanol and then dried in a vacuum at 60 °C overnight. To remove the organic residue and excess selenium powder, the as-prepared products were annealed in Ar/H₂ (95%:5%) at 300 °C for 2 h.

Growth of MoSe₂ nanoflowers on graphene: GO was made by a modified Hummers method.^[S1] Then 20 mg of GO was dispersed in 4 mL of distilled water under constant sonication at room temperature for approximately 60 min until a clear and homogeneous solution was achieved. The following steps were similar to the preparation of MoSe₂ except added above mentioned 4 mL of GO solution, the mixed solvents contains 9 mL of oleic acid, 5 mL of ethanol and 4 mL of distilled water. For comparison, the other two MoSe₂/rGO hybrid nanostructures with different graphene and MoSe₂ ratios were prepared: one is with 0.5 mmol of (NH₄)₂MoO₄, 1.0 mol of Se and 10 mg of GO; and the other is with 0.5 mmol of (NH₄)₂MoO₄, 1.0 mol of Se and 30 mg of GO.

Characterizations: TEM images were acquired by a Hitachi HT-7700 transmission electron microscope (TEM, Japan) operating at 100 kV. High-resolution TEM (HRTEM) micrographs were obtained with a Philips Tecnai F20 FEG-TEM (The USA) operated at 200 kV. Samples for TEM analysis were prepared by drying a drop of cyclohexane solution containing the nanomaterials on the surface of a carbon-coated copper grid. Raman spectrum of powder samples were recorded on LabRAM HR Raman microscope with a laser excitation wavelength of 532 nm. The X-ray diffraction XRD patterns were obtained using a Rigaku D/MAX-RB with monochromatized Cu K α radiation ($\lambda=1.5418$ Å) in the 2 θ ranging from 10° to 80°. Infrared spectra were recorded on a Nicolet 6700 FTIR spectrometer. X-ray photoelectron spectra (XPS) were conducted using a PHI Quantera SXM instrument equipped with an Al X-ray excitation source (1486.6 eV). Binding energies (BEs) are referenced to the C 1s of carbon contaminants at 284.6 eV. All samples were prepared by depositing a thin layer of products onto a cleaned Si wafer and drying at room temperature.

Electrocatalytic measurements for HER: Typically, 4 mg of sample and 30 μ L Nafion solution (5 wt%) were dispersed in 1 mL water-ethanol solution with volume ratio of 1:1 by sonicating for 1 h to form a homogeneous ink. Then 5 μ L of the dispersion (containing 20 μ g of catalyst) was loaded onto a rotating disk electrode (RDE) with 3 mm diameter (loading ca. 0.285 mg cm⁻²). Linear sweep voltammetry with scan rate of 5 mV s⁻¹ was conducted in 0.5 M H₂SO₄ (purged with pure N₂) using electrochemical cell setup, with a saturated calomel electrode (Hg/HgCl₂ in saturated KCl) as the reference electrode and a Pt wire as the counter electrode, and RDE as the working electrode with a rotating speed of 2000 rpm. All the potentials were converted to values with reference to a reversible hydrogen electrode (RHE). Cyclic voltammetry was conducted at room temperature by using the same standard three-electrode setup ranging from 0.1 to -0.3 V (vs RHE) at a scan rate of 50 mV s⁻¹. Time-dependent current density curve of MoSe₂/rGO hybrid nanostructures was conducted under static overpotential of 200 mV for continuous operation of 6000 seconds. Nyquist plots of as-prepared MoSe₂ and MoSe₂/rGO hybrid were measured at overpotential of 250 mV from 100 kHz to 0.1 Hz with amplitudes of 5 mV.

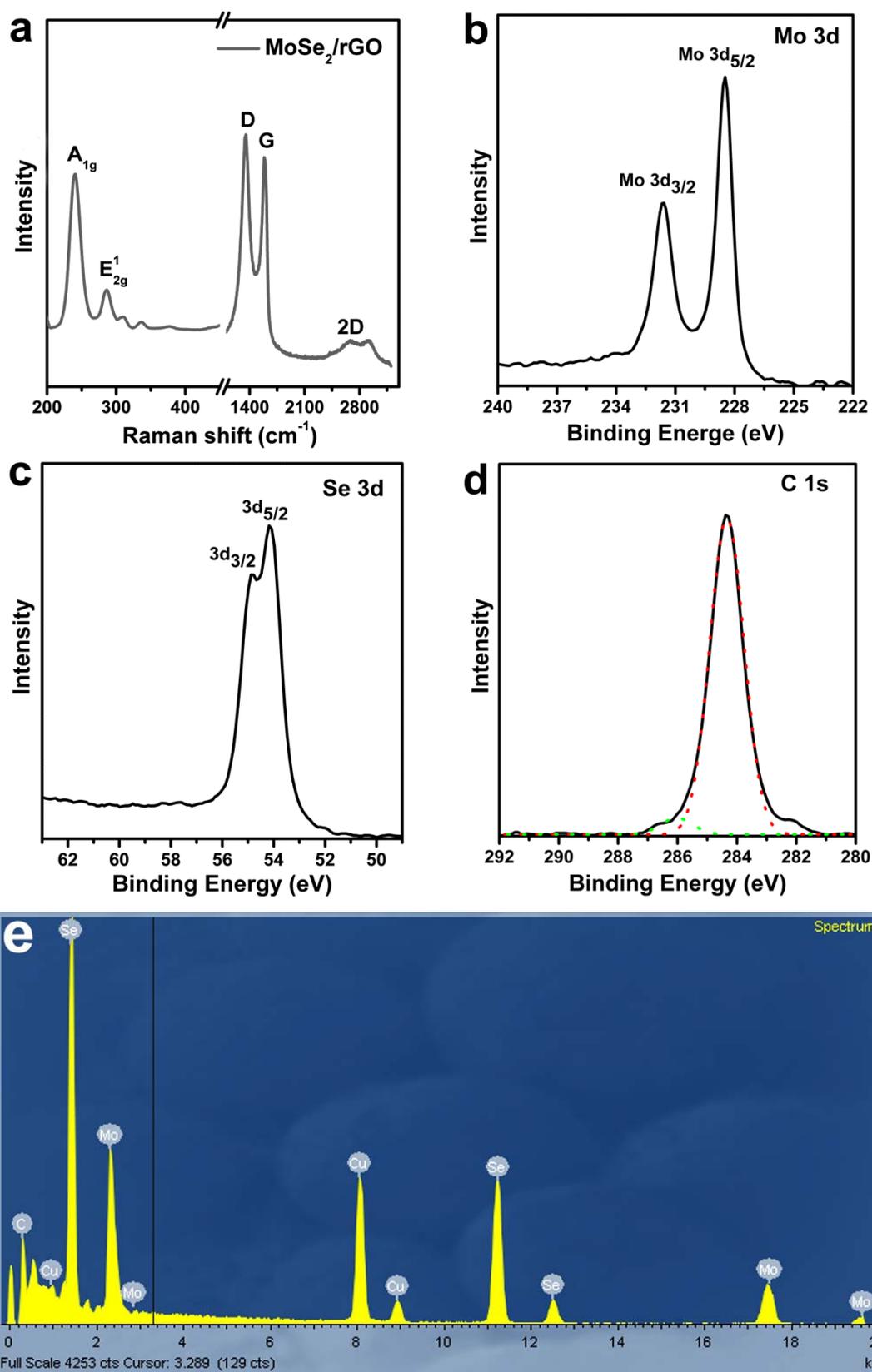


Fig. S1. (a) Raman spectrum and (b-d) XPS spectra of as-obtained MoSe₂/rGO hybrid nanostructures. (b) Mo 3d, (c) Se 3d, and (d) C 1s signals recorded for MoSe₂/rGO hybrid nanostructures. (e) Energy-dispersive X-ray analysis (EDX) spectrum of MoSe₂, note that the Cu signals are from the TEM copper grid substrate.

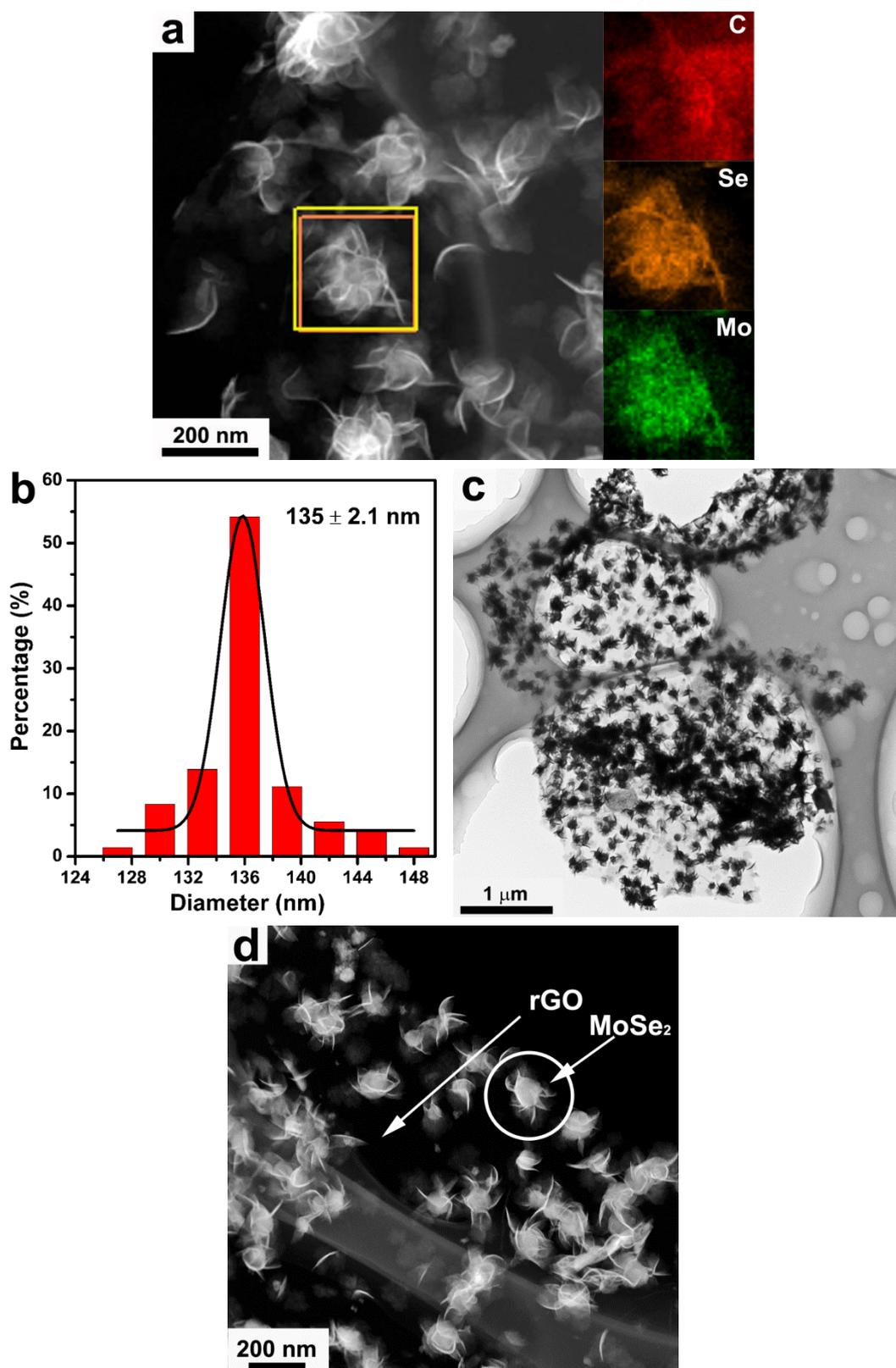


Fig. S2. (a) STEM image and EDX elemental mappings of MoSe₂/rGO hybrid. (b) Size distribution histogram showing narrow size distribution of MoSe₂ on the graphene surface. (c) 3D MoSe₂ nanoflowers grown on graphene in the MoSe₂/rGO hybrid nanostructures, with no free MoSe₂ nanostructures can be observed. (d) HAADF-STEM image of MoSe₂/rGO hybrid nanostructures. From the elemental mapping results, the Mo, Se, and C elements are clearly evidenced in the MoSe₂/rGO hybrid, and the distributions and intensities of the signals match well with the MoSe₂ nanosheets and rGO structures shown in the STEM image.

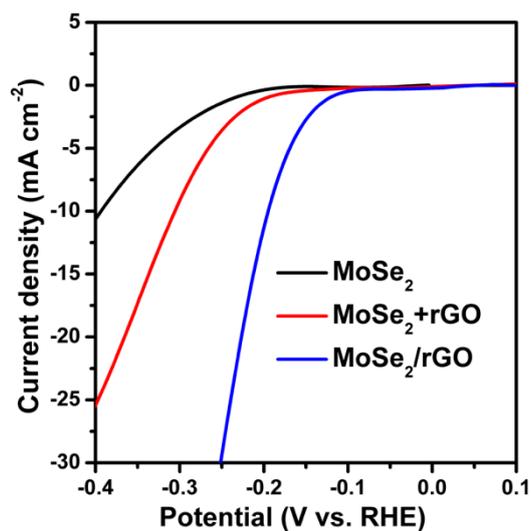


Fig. S3. Polarization curve of MoSe₂ nanosheets physically mixed with rGO (0.5 mmol:20 mg), with its performance inferior to MoSe₂/rGO hybrid nanostructures.

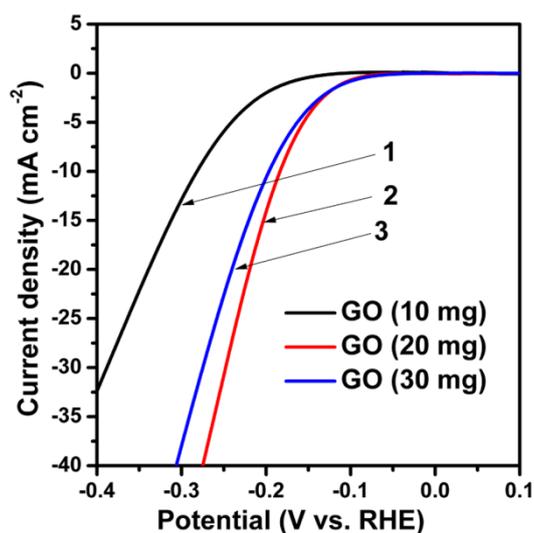


Fig. S4. Polarization curves recorded on glassy carbon electrodes with catalysts of MoSe₂/rGO hybrid nanostructures with different ratios. Conditions: loading of 0.285 mg cm⁻², potential scan rate of 5 mV s⁻¹, electrode rotating rate of 2000 rpm. The line 1 0.5 mmol (NH₄)₂MoO₄, 1.0 mol Se and 10 mg GO, line 2 0.5 mmol (NH₄)₂MoO₄, 1.0 mol Se and 20 mg GO, and line 3 0.5 mmol (NH₄)₂MoO₄, 1.0 mol Se and 30 mg GO.

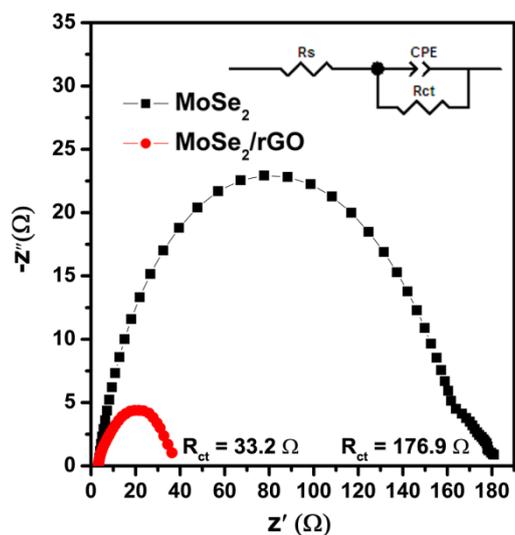


Fig. S5. Nyquist plots of the MoSe_2 and MoSe_2/rGO hybrid nanostructures, showing the imaginary part versus the real part of impedance. The MoSe_2/rGO hybrid only showed a charge transfer resistance (R_{ct}) of around 33.2 Ω , which is much smaller than R_{ct} of MoSe_2 nanosheets (176.9 Ω). This also demonstrates that the rGO can dramatically enhance the electron transfer.

Reference:

[S1] D. C. Marcano, D. V. Kosynkin, J. M. Berlin, A. Sinitskii, Z. Z. Sun, A. Slesarev, L. B. Alemany, W. Lu, J. M. Tour, *ACS Nano* 2010, **4**, 4806.